

Solution Processing of Semiconducting Organic Molecules for Tailored Charge Transport Properties

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We studied the charge transport characteristics of the organic semiconductor 6,13-bis(tri isopropyl silyl ethynyl) pentacene (TIPS-PEN) deposited by dip-coating of a solution in an azeotropic solvent mixture. Arrays of crystalline ribbons were obtained with a morphology controllable by variation of the coating speed U . The charge carrier mobility μ exhibited a systematic and reproducible dependence on the coating speed U and maximum values as high as $\mu \approx 1.0 \text{ cm}^2/(\text{V s})$. [1]

We used isopropanol (IPA) and toluene, which exhibit a positive azeotropic point at a volume fraction (VF) of approximately 1/1. We typically use IPA/toluene VFs above 55/45, such that the vapor concentration of toluene exceeded its concentration in the liquid phase, which tends to enrich in IPA over time. The TIPS-PEN concentration was 1.5 wt%. In Fig. 2 we show the dependence of the average ribbon width $\langle w \rangle$ and the fill factor f that were extracted from the optical microscopy images.

The ribbon width monotonically decreases with increasing dip-coating speed. The solid line corresponds to a power-law relation $\langle w \rangle = b(U/U_0)^\alpha$ with $U_0 = 0.12 \text{ mm/s}$ and fit parameters $b = 5.5 \text{ }\mu\text{m}$ and $\alpha = 0.94$. Figure 3 presents the dependence of the field effect mobility μ on the dip-coating speed. A very well-defined maximum of the carrier mobility $\mu_{\text{max}} \approx 0.75 \text{ cm}^2/(\text{V s})$ is observed in the vicinity of $U_{\text{opt}} = 0.02 \text{ mm/s}$.

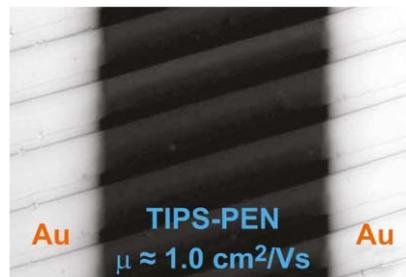


Fig. 1: Optical micrograph of TIPS-PEN crystal ribbons deposited on a Si substrate by means of solution crystallization. The white regions have increased reflectivity due to evaporated Au layers that form the source and drain contacts. Image width $200 \text{ }\mu\text{m}$.

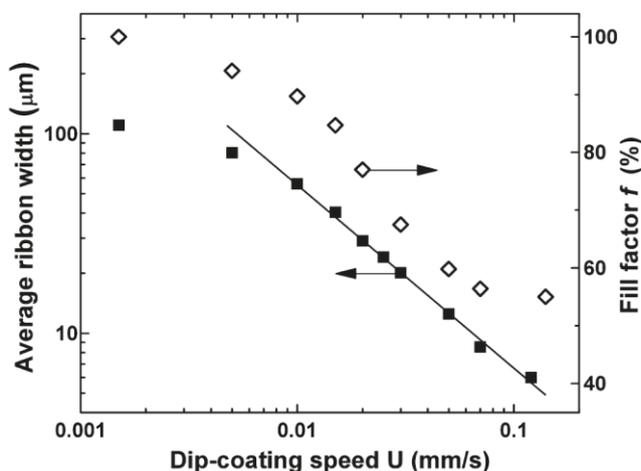


Fig. 2: Average TIPS-PEN ribbon width $\langle w \rangle$ and fill factor f as a function of U .

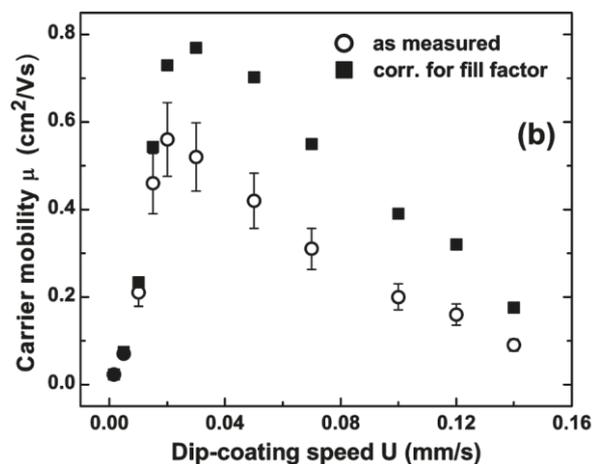


Fig. 3: Saturated carrier mobility μ vs U .

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References

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